a plurality of fins comprised of said second semiconductor material on said reduced thickness mandrel structure; and

performing at least one fourth etching process to selectively remove at least a portion of said reduced thickness mandrel structure so as to thereby expose at least a portion of each of said fins.

39. The method of claim 38, wherein, after performing said at least one third etching process, said plurality of fins are positioned under portions of said patterned mask layer.

40. A device formed in accordance with the method of any one of the preceeding claims.